ONR Progress Report 7/1/90 - 12/30/90 Karen K. Gleason N00014-90-J-1901

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Three CVD diamond films were produced in a hot-filament reactor using acetone as the carbon source. The acetone was enriched 33% at the methyl carbon, and the total gas-phase concentrations were 5.3%, 6.4%, and 7.4%. Static solid-state NMR measurements of hydrogen concentration, sp²/sp³ carbon bonding environments, and carbon-13 spin-lattice relaxation have been made on these films while they remain intact on their substrates. The hydrogen concentration was found to be below 1 at. % in each film. Increasing sp² content is found with increasing gas-phase carbon concentration. Ongoing measurements are aimed at understanding the sp³ region of the NMR spectra and its relationship to Raman measurements of these films. An increased concentration of defect centers decreased the spin-lattice relaxation time constant from 18 s to 1 s as the gas-phase carbon concentration increased.

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Karen K. Gleason
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artifact Diamond Characterization

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